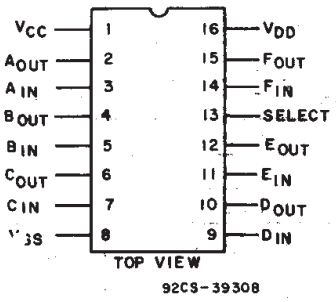
CD4504



TERMINAL ASSIGNMENT

CMOS Hex Voltage-Level Shifter for TTL-to-CMOS or CMOS-to-CMOS Operation

High-Voltage Types (20-Volt Rating)

Features:

- *Independence of power-supply sequence considerations-V_{CC} can exceed V_{DD}; input signals can exceed both V_{CC} and V_{DD}*
- *Up and down level-shifting capability*
- *Shiftable input threshold for either CMOS or TTL compatibility*
- *Standardized symmetrical output characteristics*
- *100% tested for quiescent current @ 20 V*
- *Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25° C*
- *5 V, 10 V, and 15 V parametric ratings*
- *Meets all requirements of JEDEC Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"*

■ CD4504B hex voltage level-shifter consists of six circuits which shift input signals from the V_{CC} logic level to the V_{DD} logic level. To shift TTL signals to CMOS logic levels, the SELECT input is at the V_{CC} HIGH logic state. When the SELECT input is at a LOW logic state, each circuit translates signals from one CMOS level to another.

The CD4504B device is supplied in 16-lead ceramic dual-in-line packages (D and F suffixes), 16-lead plastic dual-in-line packages (E suffix), 16-lead dual-in-line surface-mount plastic packages (M suffix), and in chip form (H suffix).

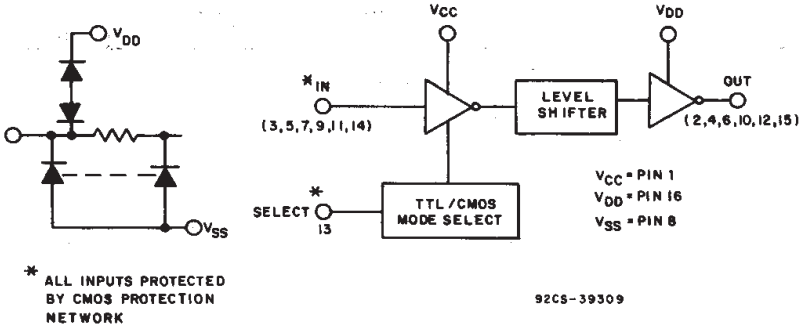


Fig. 1 - Functional diagram for CD4504B.

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
(Voltages referenced to V_{SS} Terminal) ..... -0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS ..... -0.5V to V_{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT ..... ±10mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = -55°C to +100°C 500mW
For T_A = +100°C to +125°C ..... Derate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) 100mW
OPERATING-TEMPERATURE RANGE (T_A) ..... -55°C to +125°C
STORAGE TEMPERATURE RANGE (T_{stg}) ..... -65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max ..... +265°C

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC		CONDITIONS				LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
		V_O (V)	V_{IN} (V)	V_{CC} (V)	V_{DD} (V)	-55	-40	+85	+125	+25 MIN	+25 TYP	+25 MAX	
Quiescent Device Current, I_{DD} Max and I_{CC} in CMOS-CMOS Mode		—	0, 5	5	5	1	1	30	30	—	0.02	1	µA
		—	0, 10	5	10	2	2	60	60	—	0.02	2	
		—	0, 15	5	15	4	4	120	120	—	0.02	4	
		—	0, 20	5	20	20	20	600	600	—	0.04	20	
Quiescent Device Current, I_{CC} Max TTL-CMOS Mode		—	0, 5	5	5	5	5	6	6	—	2.5	5	mA
		—	0, 10	5	10	5	5	6	6	—	2.5	5	
		—	0, 15	5	15	5	5	6	6	—	2.5	5	
Output Low (Sink) Current, I_{OL} Min		0.4	0.5	—	5	0.64	0.61	0.42	0.36	0.51	1	—	mA
		0.5	0, 10	—	10	1.6	1.5	1.1	0.9	1.3	2.6	—	
		1.5	0, 15	—	15	4.2	4	2.8	2.4	3.4	6.8	—	
Output High (Source) Current, I_{OH} Min		4.6	0, 5	—	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	—	
		2.5	0, 5	—	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	—	
		9.5	0, 10	—	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	—	
		13.5	0, 15	—	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	—	
Output Voltage: Low-Level, V_{OL} Max		—	0, 5	—	5	0.05				—	0	0.05	V
		—	0, 10	—	10	0.05				—	0	0.05	
		—	0, 15	—	15	0.05				—	0	0.05	
Output Voltage: High-Level, V_{OH} Min		—	0, 5	—	5	4.95				4.95	5	—	
		—	0, 10	—	10	9.95				9.95	10	—	
		—	0, 15	—	15	14.95				14.95	15	—	
Input Low Voltage, V_{IL} Max Note 1	TTL-CMOS	1	—	5	10	0.8				—	—	0.8	
	TTL-CMOS	1	—	5	15	0.8				—	—	0.8	
	CMOS-CMOS	1	—	5	10	1.5				—	—	1.5	
	CMOS-CMOS	1.5	—	5	15	1.5				—	—	1.5	
	CMOS-CMOS	1.5	—	10	15	3				—	—	3	
Input High Voltage, V_{IH} Min Note 1	TTL-CMOS	9	—	5	10	2				2	—	—	
	TTL-CMOS	13.5	—	5	15	2				2	—	—	
	CMOS-CMOS	9	—	5	10	3.5				3.5	—	—	
	CMOS-CMOS	13.5	—	5	15	3.5				3.5	—	—	
	CMOS-CMOS	13.5	—	10	15	7				7	—	—	
Input Current, I_{IN} Max		—	0, 18	—	18	±0.1	±0.1	±1	±1	—	$\pm 10^{-5}$	±0.1	µA

Note 1: Applies to the 6 input signals. For mode control (P13), only the CMOS-CMOS ratings apply.

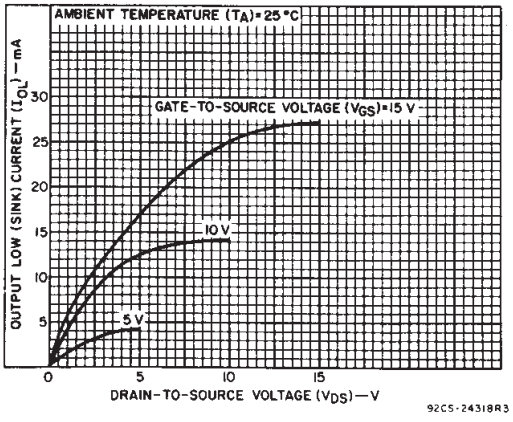


Fig. 2 - Typical output low (sink) current characteristics.

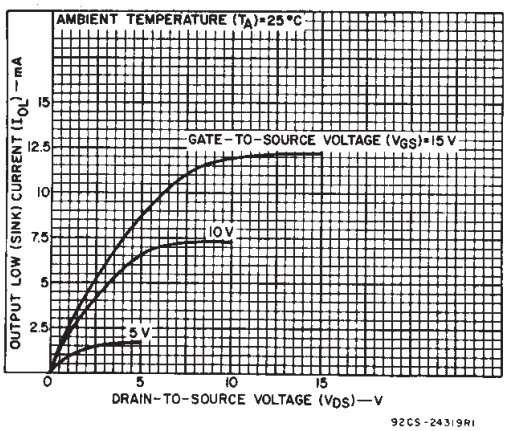


Fig. 3 - Minimum output low (sink) current characteristics.

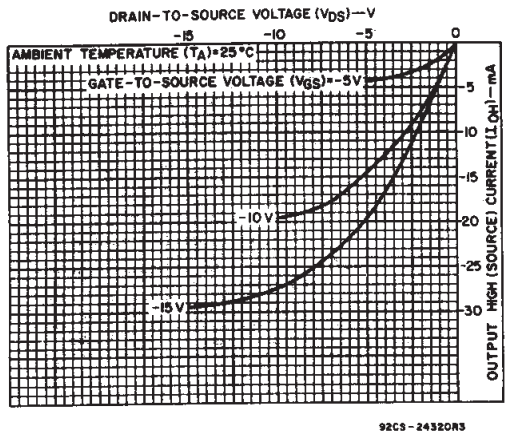


Fig. 4 - Typical output high (source) current characteristics.

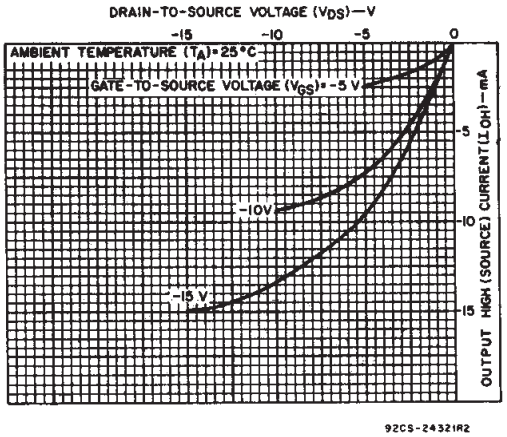


Fig. 5 - Minimum output high (source) current characteristics.

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	V_{DD} (V)	LIMITS		UNITS
		Min.	Max.	
Supply-Voltage Range (For T_A = Full Package-Temperature Range)	—	3	18	V

DYNAMIC ELECTRICAL CHARACTERISTICS, At T_A = 25°C; Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200 Ω

CHARACTERISTIC		SHIFTING MODE	VCC (V)	VDD (V)	LIMITS		UNITS
					TYP.	MAX.	
Propagation Delay: High-to Low,	t_{PHL}	TTL to CMOS $V_{DD} > V_{CC}$	5	10	140	280	ns
			5	15	140	280	
		CMOS to CMOS $V_{DD} > V_{CC}$	5	10	120	240	
			5	15	120	240	
			10	15	70	140	
		CMOS to CMOS $V_{CC} > V_{DD}$	10	5	275	550	
			15	5	275	550	
			15	10	70	140	
Low-to-High,	t_{PLH}	TTL to CMOS $V_{DD} > V_{CC}$	5	10	140	280	
			5	15	140	280	
		CMOS to CMOS $V_{DD} > V_{CC}$	5	10	120	240	
			5	15	120	240	
			10	15	70	140	
		CMOS to CMOS $V_{CC} > V_{DD}$	10	5	200	400	
			15	5	200	400	
			15	10	60	120	
Transition Time,	t_{THL}, t_{TLH}	All Modes		5	100	200	
				10	50	100	
				15	40	80	
Input Capacitance,	C_{IN}	Any Input			5	7.5	pF

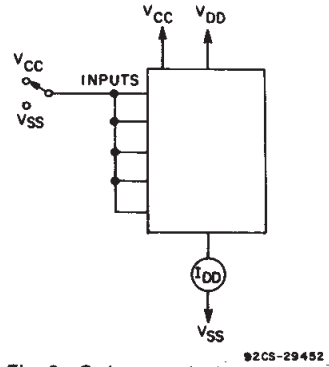


Fig. 6 - Quiescent device current.

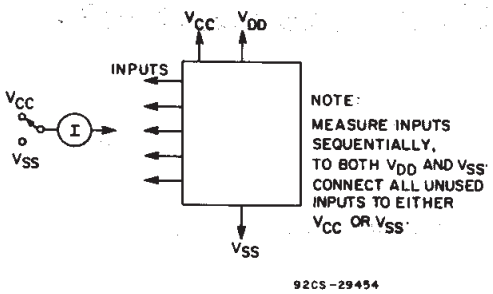


Fig. 7 - Input current.

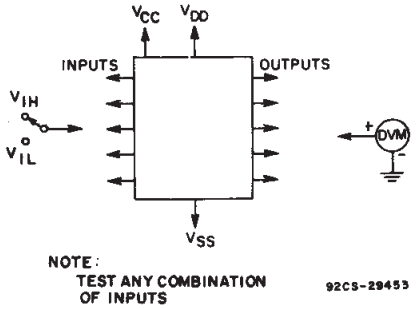


Fig. 8 - Input voltage.

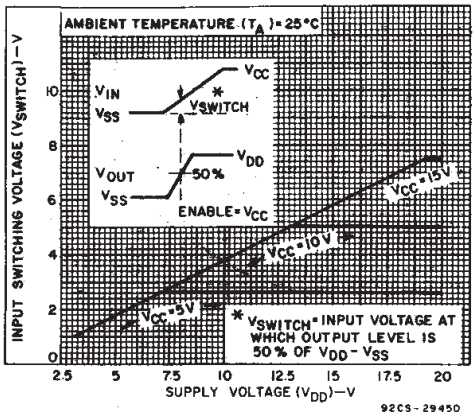


Fig. 9 - Typical input switching as a function of high-level supply voltage. (SELECT at V_{CC}-CMOS mode).

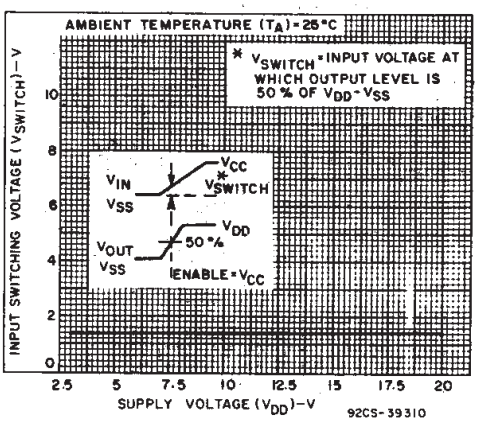


Fig. 10 - Typical input switching as a function of high-level supply voltage (SELECT at V_{SS}-TTL mode).

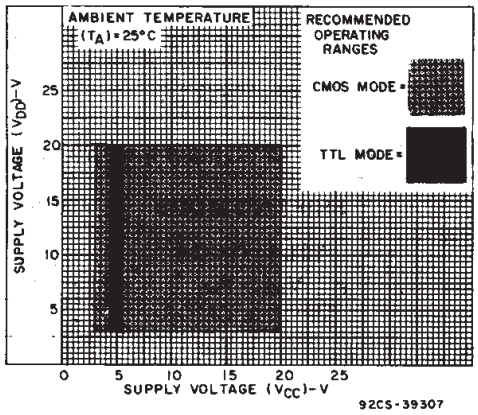
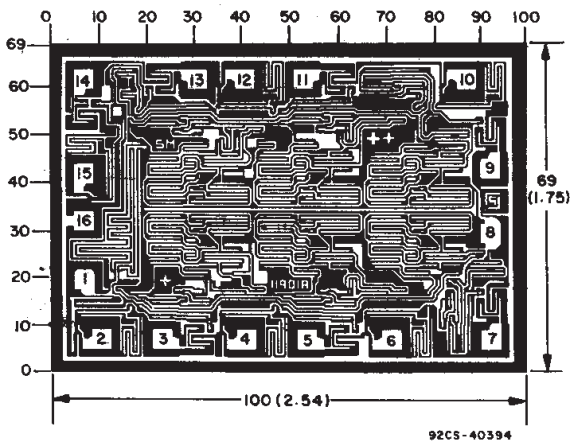


Fig. 11 - High-level supply voltage vs. low-level supply voltage.



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

Dimensions and pad layout for CD4504BH.